

Title (en)

METHOD FOR PRODUCING A MICROELECTRONIC STRUCTURE

Title (de)

VERFAHREN ZUR HERSTELLUNG EINER MIKROELEKTRONISCHEN STRUKTUR

Title (fr)

PROCEDE DE PRODUCTION D'UNE STRUCTURE MICROELECTRONIQUE

Publication

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Application

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Priority

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Abstract (en)

[origin: DE19911150C1] Microelectronic structure production, comprising physically etching a conductive layer (45) from a substrate (5) such that removed material is transferred onto a layer structure side wall (35), is new. A microelectronic structure production process comprises (a) partially covering a substrate (5) with a layer structure (30) including one or more first conductive layers (15, 20) which extend to the layer structure side wall (35); (b) applying a second conductive layer (45) onto the layer structure and the substrate; and (c) removing the second conductive layer (45) from the substrate by a physical etching process such that the removed material deposits on the layer structure side wall. Preferred Features: The first conductive layer (15, 20) is a barrier and/or bond layer of a titanium nitride/titanium or tantalum nitride/tantalum combination and the second conductive layer (45) consists of Pt. The layer stack (30) is subsequently covered with a dielectric layer of formula ABO_x or DO_x, where A = one or more of Sr, Bi, Nb, Pb, Zr, La, Li, K, Ca and Ba, B = one or more of Ti, Nb, Ru, Mg, Mn, Zr and Ta, D = Ti or Ta and x = 2 to 12.

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